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MB05S
THRU
MB10S

Features

- Surface Mount Package
- Glass Passivated Diode Construction
- Moisture Resistant Epoxy Case
- High Surge Current Capability

Maximum Ratings

- Operating Temperature: -55°C to +150°C
- Storage Temperature: -55°C to +150°C

Catalog Number	Device Marking	Maximum Rccurent Peak Reverse Voltage	Maximum RMS Voltage	Maximum DC Blocking Voltage
MB05S	MB05S	50V	35V	50V
MB1S	MB1S	100V	70V	100V
MB2S	MB2S	200V	140V	200V
MB4S	MB4S	400V	280V	400V
MB6S	MB6S	600V	420V	600V
MB8S	MB8S	800V	560V	800V
MB10S	MB10S	1000V	700V	1000V

Electrical Characteristics @ 25°C Unless Otherwise Specified

Average Forward Current	$I_{F(AV)}$	0.5A 0.8A	Note1 Note2
Peak Forward Surge Current	I_{FSM}	30A	8.3ms, half sine
Maximum Instantaneous Forward Voltage	V_F	1.0V	$I_{FM} = 0.4A$, per leg. $T_A = 25^\circ C$
Maximum DC Reverse Current At Rated DC Blocking Voltage	I_R	5 μA	$T_A = 25^\circ C$
Typical Junction Capacitance	C_J	25pF	Measured at 1.0MHz, $V_R = 4.0V$

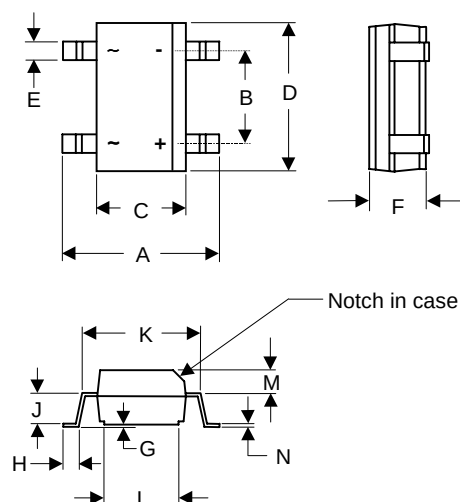
Note1. Measured at 1.0 MHz and applied reverse voltage of 4.0 Volts

Note2. On alum: substrate P.C.B with an rea of 0.8 x 0.8 x 0.25"
(20 x 20 x 6.4mm) mounte on 0.05 x 0.05 "(13 x 13 mm)
solder pad.

*Pulse Test: Pulse Width 300 μ sec, Duty Cycle 1%

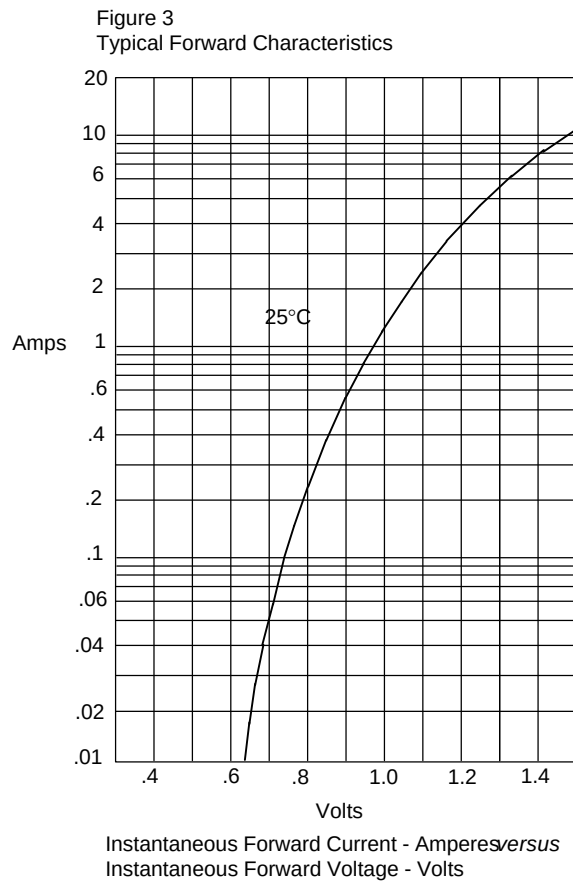
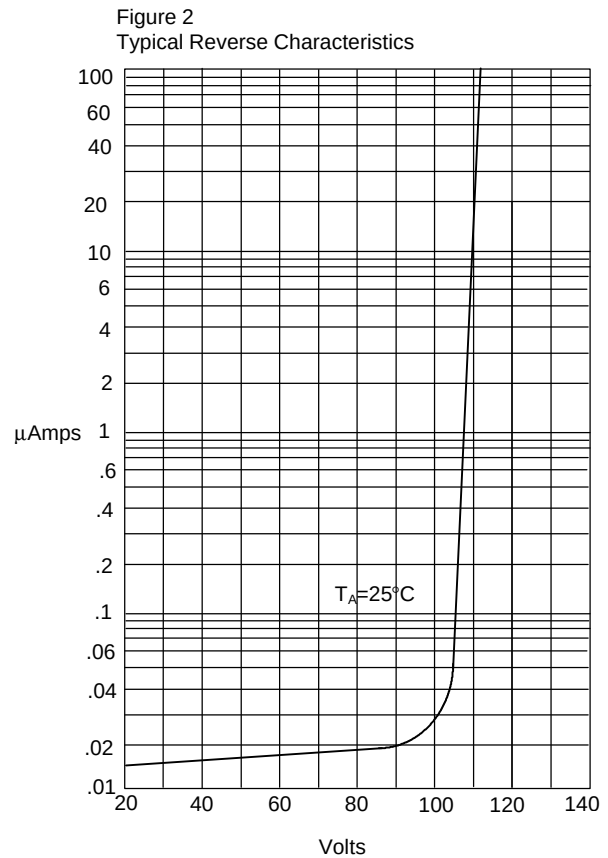
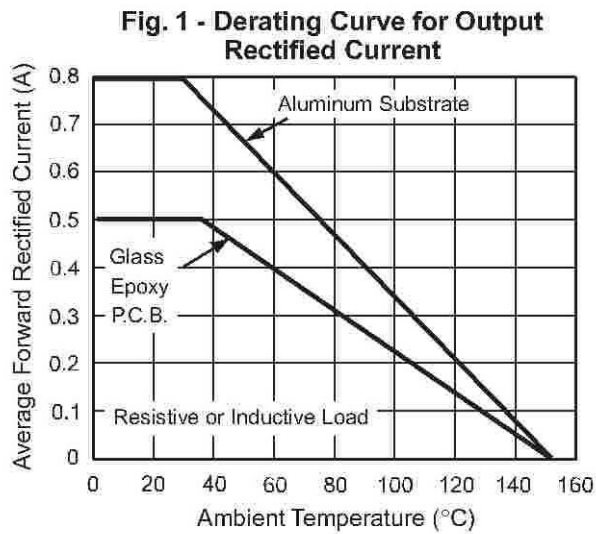
0.5Amp Single Phase Glass Passivated Bridge Rectifier 50 to 1000 Volts

MBS -1



DIM	INC HES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.252	.272	6.40	6.90	
B	.095	.105	2.41	2.67	
C	.144	.161	3.65	4.10	
D	.179	.195	4.55	4.95	
E	.017	.029	0.43	0.74	
F	.090	.106	2.30	2.70	
G	.004	.008	0.10	0.20	
H	.019	.038	0.48	0.96	
J	.058	.062	1.47	1.57	
K	.195	.205	4.95	5.21	
L	.110	.114	2.80	2.90	
M	.039	.049	0.99	1.24	
N	.006	.016	0.15	0.41	

MB05S thru MB10S



Instantaneous Reverse Leakage Current - MicroAmperes versus Percent Of Rated Peak Reverse Voltage - Volts

